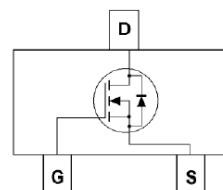


N-Channel Enhancement Mode MOSFET

Feature

- 30V/1A, $R_{DS(ON)} = 750\text{m}\Omega$ (MAX) @ $V_{GS} = 10\text{V}$, $I_{DS} = 0.60\text{A}$
 $R_{DS(ON)} = 900\text{m}\Omega$ (MAX) @ $V_{GS} = 4.5\text{V}$, $I_{DS} = 0.20\text{A}$
- Super High dense cell design for extremely low $R_{DS(ON)}$.
- Reliable and Rugged.
- SOT-23 for Surface Mount Package.



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	1	A

Electrical Characteristics $T_A = 25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	VGS=0V, ID=250μA	30	-	-	V
Zero-Gate Voltage Drain Current	IDSS	VDS=24V, VGS=0V	-	-	1	μA
Gate Body Leakage Current, Forward	IGSSF	VGS=20V, VDS=0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	VGS=-20V, VDS=0V	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	VGS(th)	VGS= VDS, ID=250μA	1	-	-	V
Static Drain-source	RDS(ON)	VGS =10V, ID =0.6A	-	-	750	m Ω
On-Resistance		VGS =4.5V, ID =0.2A	-	-	900	m Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	VGS =0V, IS=0.23A			1.2	V